MG6403WZ

650V 80A Insulated Gate Bipolar Transistor

Datasheet

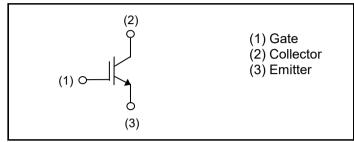
| V_{CES} | 650V |
|-------------------------------|--------|
| I _{C (Nominal)} | 80A |
| V _{CE(sat) (Typ.)} | 1.5V |
| Max. Possible Chips per Wafer | 444pcs |

● Outline Wafer

Features

- 1) Trench Light Punch Through Type
- 2) Low Collector Emitter Saturation Voltage
- 3) High Speed Switching & Low Switching Loss
- 4) Short Circuit Withstand Time 2µs

●Inner Circuit



Application

Solar Inverter

UPS

Welding

ΙH

PFC

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|--------------------------------|--------------------|-------------|------|
| Collector - Emitter Voltage | V _{CES} | 650 | V |
| Gate - Emitter Voltage | V_{GES} | ±30 | V |
| Collector Current | I _C *1 | *1) | Α |
| Pulsed Collector Current | I _{CP} *2 | 320 | Α |
| Operating Junction Temperature | T _j | -40 to +175 | °C |

^{*1} Depending on thermal properties of assembly

^{*2} Pulse width limited by $T_{jmax.}$

●Design Assurance

| Parameter | Symbol | Conditions | | Values | | Unit | |
|----------------------------------|--------------------|---|-------------|--------|------|-------|--|
| raiailletei | Symbol | Conditions | Min. | Тур. | Max. | Offic | |
| | | $V_{CC} \le 360V$, | | | | | |
| Short Circuit Withstand Time | t _{sc} *3 | $V_{CC} \le 360V$, $V_{GE} = 15V$, $T_i = 25^{\circ}C$ | 2 | - | - | μs | |
| | | T _j = 25°C | | | | | |
| | | $I_C = 320A, V_{CC} = 520V,$ | | | | | |
| Reverse Bias Safe Operating Area | RBSOA*3 | $I_C = 320A$, $V_{CC} = 520V$, $V_P = 650V$, $V_{GE} = 15V$, $R_G = 100\Omega$, $T_j = 175^{\circ}C$ | FULL SQUARE | | - | | |
| | | $R_G = 100\Omega, T_j = 175^{\circ}C$ | | | | | |

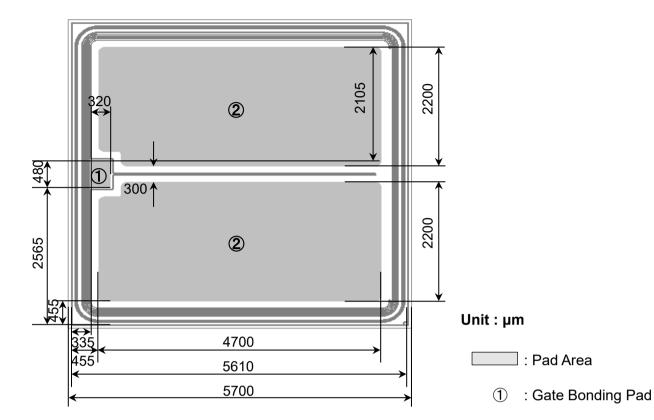
^{*3} Design assurance without measurement

●Electrical Characteristics (at T_i = 25°C unless otherwise specified, in case of TO-247N package)

| Devementer | Developed Constitutions | | Values | | | l locit |
|---|-------------------------|---|--------|-------------|----------|---------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
| Collector - Emitter Breakdown Voltage | BV _{CES} | $I_{C} = 10 \mu A, V_{GE} = 0 V$ | 650 | 1 | - | ٧ |
| Collector Cut - off Current | I _{CES} | $V_{CE} = 650V, V_{GE} = 0V$ | - | - | 10 | μΑ |
| Gate - Emitter Leakage Current | I _{GES} | $V_{GE} = \pm 30V$, $V_{CE} = 0V$ | - | ı | ±200 | nA |
| Gate - Emitter Threshold Voltage | $V_{GE(th)}$ | $V_{CE} = 5V, I_{C} = 57.1 \text{mA}$ | 5.0 | 6.0 | 7.0 | V |
| Collector - Emitter Saturation Voltage | V _{CE(sat)} *3 | $I_{C} = 80A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$ | - | 1.5 1.85 | 1.9 - | V |
| Input Capacitance | C _{ies} | V _{CE} = 30V, | - | 4810 | - | |
| Output Capacitance | C _{oes} | V _{GE} = 0V, | - | 184 | - | pF |
| Reverse transfer Capacitance | C_{res} | f = 1MHz | - | 79 | - | |
| Total Gate Charge | Q_g | V _{CE} = 400V, | - | 171 | - | |
| Gate - Emitter Charge | Q_ge | I _C = 80A, | - | 33 | - | nC |
| Gate - Collector Charge | Q_{gc} | V _{GE} = 15V | - | 59 | - | |

^{*3} Design assurance without measurement

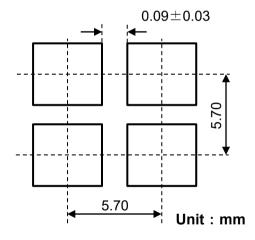
●Chip Information



Backside: Collector

: Emitter Bonding Pad

2



| Wafer Size | 150mm |
|-------------------------|-----------------------|
| Wafer Thickness | 0.07±0.01mm |
| Chip Size | 5.70mm×5.70mm |
| Cut Line Width | 0.09±0.03mm |
| Top Side Metallization | AlSiCu:4.4µm |
| Back Side Metallization | Ti/Ni:0.4µm/Au:0.05µm |
| Passivation | Polyimide |
| | · |

•Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

| This chip data sheet refers to the device data sheet | RGTVX6TS65 |
|--|------------|
| | |

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